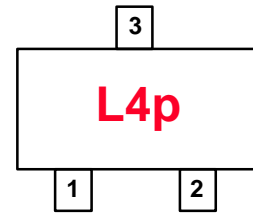


BAT54 series
SCHOTTKY BARRIER DIODES

DISCRETE POWER AND SIGNAL
TECHNOLOGIES



PACKAGE
TO-236AB (Low)

MARKING
BAT54 L4p BAT54C L43
BAT54A L42 BAT54S L44

Absolute Maximum Ratings* TA=25°C unless otherwise noted

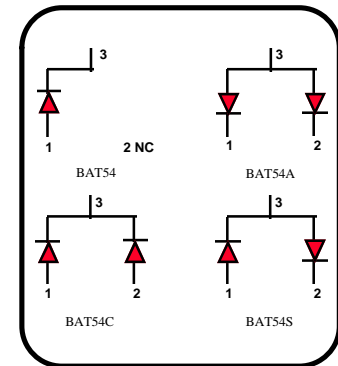
Parameter	Value	Units
Storage Temperature	-55 to +150	°C
Operating Junction Temperature	+150	°C
Working Inverse Voltage	25	V
DC Forward Current (IF)	200	mA
Recurrent Peak Forward Current (IFRM)	300	mA
Peak Forward Surge Current (IFSM) Pulse Width = 1.0 Second	600	mA
Total Power Dissipation at 25°C	230	mW
Theta (Rth j-a) (Note 1)	430	°K/W

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired

NOTES:

1) From junction to ambient mounted on a ceramic substrate of 10 mm x 8 mm x 0.6 mm

CONNECTION DIAGRAMS



Electrical Characteristics TA = 25°C unless otherwise noted

SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
B _V	Breakdown Voltage	30		V	I _R = 10 uA
I _R	Reverse Leakage		2.0	uA	V _R = 25 V
V _F	Forward Voltage		240 320 400 500 1.0	mV mV mV mV V	I _F = 100 uA I _F = 1.0 mA I _F = 10 mA I _F = 30 mA I _F = 100 mA
C _T	Capacitance		10	pF	V _R = 1.0 V f = 1.0 MHz
T _{RR}	Reverse Recovery Time		5.0	nS	I _F = I _R = 10 mA I _{RR} = 1.0 mA R _L = 100 Ohms